

## NTE2582 Silicon NPN Transistor High Speed Switching Regulator

**Features:**

- High Breakdown Voltage and High Reliability
- Fast Switching Speed
- Wide ASO

**Absolute Maximum Ratings:** ( $T_A = +25^\circ\text{C}$  unless otherwise specified)

Collector–Base Voltage, $V_{CBO}$ .....	500V
Collector–Emitter Voltage, $V_{CEO}$ .....	400V
Emitter–Base Voltage, $V_{EBO}$ .....	7V
Collector Current, $I_C$	
Continuous .....	12A
Pulsed (Note 1) .....	25A
Collector Dissipation ( $T_A = +25^\circ\text{C}$ ), $P_C$ .....	2W
Collector Dissipation ( $T_C = +25^\circ\text{C}$ ), $P_C$ .....	40W
Operating Junction Temperature, $T_J$ .....	+150°C
Storage Temperature Range, $T_{stg}$ .....	–55° to +150°C

Note 1. Pulse Width  $\leq 300\mu\text{s}$ , Duty Cycle  $\leq 10\%$ .

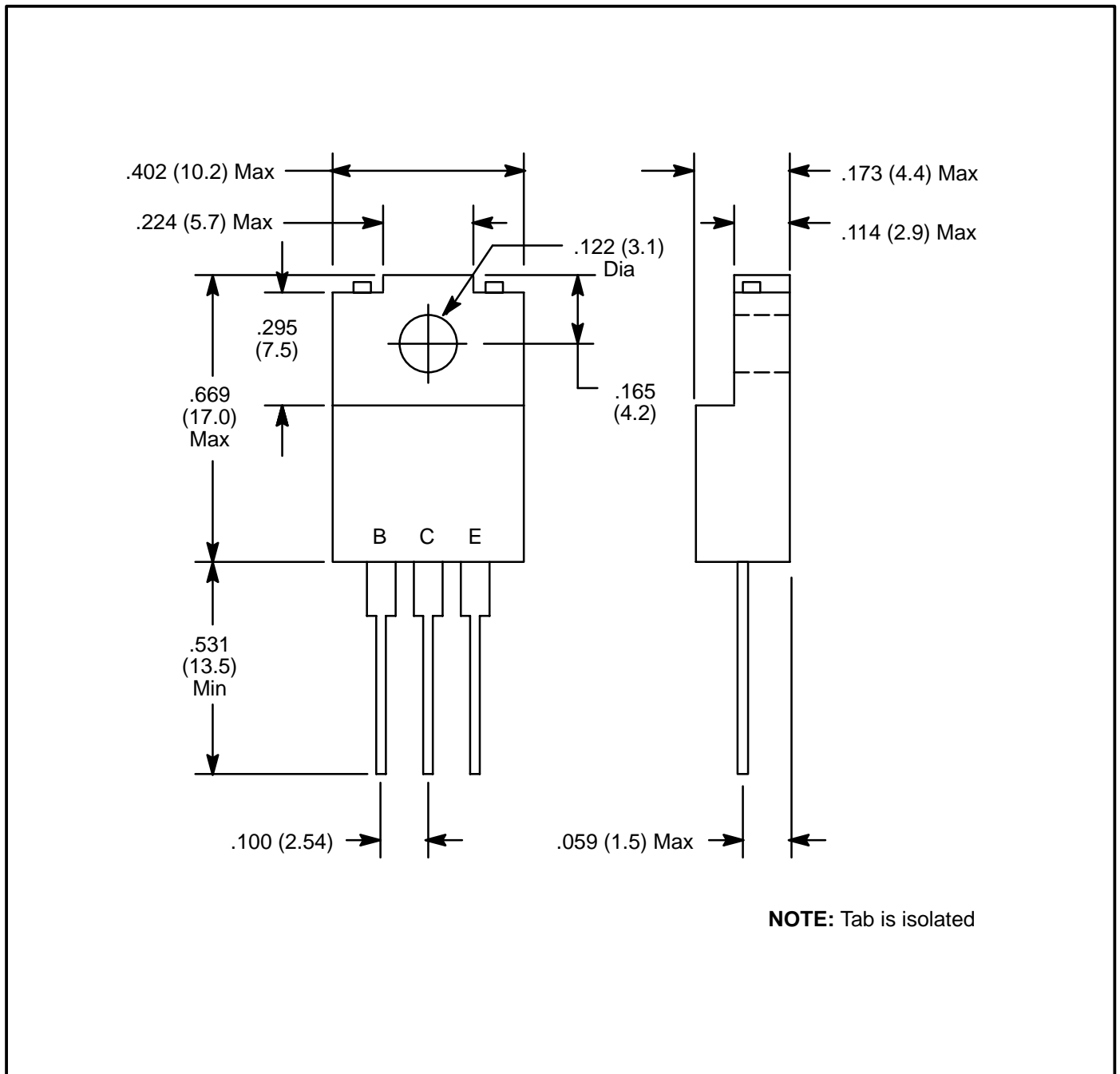
**Electrical Characteristics:** ( $T_A = +25^\circ\text{C}$  unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cutoff Current	$I_{CBO}$	$V_{CB} = 400\text{V}, I_E = 0$	–	–	10	$\mu\text{A}$
Emitter Cutoff Current	$I_{EBO}$	$V_{EB} = 5\text{V}, I_C = 0$	–	–	10	$\mu\text{A}$
DC Current Gain	$h_{FE}$	$V_{CE} = 5\text{V}, I_C = 1.6\text{A}$	20	–	50	
		$V_{CE} = 5\text{V}, I_C = 8\text{A}$	10	–	–	
		$V_{CE} = 5\text{V}, I_C = 10\text{mA}$	10	–	–	
Current Gain–Bandwidth Product	$f_T$	$V_{CE} = 10\text{V}, I_C = 1.6\text{A}$	–	20	–	MHz
Output Capacitance	$C_{ob}$	$V_{CB} = 10\text{V}, f = 1\text{MHz}$	–	160	–	pF
Collector–Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 8\text{A}, I_B = 1.6\text{A}$	–	–	0.8	V
Base–Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 8\text{A}, I_B = 1.6\text{A}$	–	–	1.5	V

**Electrical Characteristics (Cont'd):** ( $T_A = +25^\circ\text{C}$  unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = 1\text{mA}, I_E = 0$	500	-	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 10\text{mA}, R_{BE} = \infty$	400	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = 1\text{mA}, I_C = 0$	7	-	-	V
Collector-Emitter Sustaining Voltage	$V_{CEX(sus)}$	$I_C = 6\text{A}, I_{B1} = 0.6\text{A}, I_{B2} = -2.4\text{A}, L = 500\mu\text{H}, \text{Clamped}$	400	-	-	V
Turn-On Time	$t_{on}$	$I_C = 10\text{A}, I_{B1} = 2\text{A}, I_{B2} = -4\text{A}, R_L = 20\Omega, V_{CC} = 200\text{V}, \text{Note 2}$	-	-	0.5	$\mu\text{s}$
Storage Time	$t_{stg}$		-	-	2.5	$\mu\text{s}$
Fall Time	$t_f$		-	-	0.3	$\mu\text{s}$

Note 2. Pulse Width =  $20\mu\text{s}$ , Duty Cycle  $\leq 1\%$ .



## X-ON Electronics

Largest Supplier of Electrical and Electronic Components

*Click to view similar products for [Bipolar Transistors - BJT category](#):*

*Click to view products by [NTE manufacturer](#):*

Other Similar products are found below :

[619691C](#) [MCH4017-TL-H](#) [MJ15024/WS](#) [MJ15025/WS](#) [BC546/116](#) [BC556/FSC](#) [BC557/116](#) [BSW67A](#) [HN7G01FU-A\(T5L,F,T](#)  
[NJVMJD148T4G](#) [NSVMMBT6520LT1G](#) [NTE187A](#) [NTE195A](#) [NTE2302](#) [NTE2330](#) [NTE2353](#) [NTE316](#) [IMX9T110](#) [NTE63](#) [NTE65](#)  
[C4460](#) [SBC846BLT3G](#) [2SA1419T-TD-H](#) [2SA1721-O\(TE85L,F\)](#) [2SA1727TLP](#) [2SA2126-E](#) [2SB1202T-TL-E](#) [2SB1204S-TL-E](#) [2SC5488A-](#)  
[TL-H](#) [2SD2150T100R](#) [SP000011176](#) [FMC5AT148](#) [2N2369ADCSM](#) [2SB1202S-TL-E](#) [2SC2412KT146S](#) [2SC4618TLN](#) [2SC5490A-TL-H](#)  
[2SD1816S-TL-E](#) [2SD1816T-TL-E](#) [CMXT2207 TR](#) [CPH6501-TL-E](#) [MCH4021-TL-E](#) [BC557B](#) [TTC012\(Q\)](#) [BULD128DT4](#) [JANTX2N3810](#)  
[Jantx2N5416](#) [US6T6TR](#) [KSF350](#) [068071B](#)